## ABSTRACT OF THE DISCLOSURE

In a mechanochemical polishing apparatus, a SiC wafer is held on a wafer holding table. The surface of the wafer to be polished is pressed against a polishing cloth applied to a polishing platen with a predetermined processing pressure. The wafer holding table and polishing platen are then rotated to perform polishing with chemical liquid dropped on the polishing cloth. The chemical liquid includes chromium (III) oxide as abrasive grains and hydrogen peroxide water (oxidizing agent) for improving polishing efficiency.